

Description

The XXW9435 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

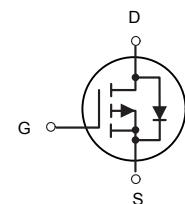


SOP-8

$V_{DS} = -30V$ $I_D = -5A$

$R_{DS(ON)} < 55\text{ m}\Omega$ @ $V_{GS}=10V$

General Features



P-Channel MOSFET

Battery protection

Load switch

Uninterruptible power supply

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Drain Current ³ , $V_{GS} @ 10V$	-5	A
IMD	Pulsed Drain Current ¹	-20	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	40	$^\circ\text{C}/\text{W}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{V}_{\text{DS}}=-24\text{V}, \text{V}_{\text{GS}}=0\text{V}$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$\text{V}_{\text{GS}}=\pm20\text{V}, \text{V}_{\text{DS}}=0\text{V}$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$\text{V}_{\text{GS(th)}}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=-250\mu\text{A}$	-1	-1.6	-3	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-5.1\text{A}$	-	43	55	$\text{m}\Omega$
		$\text{V}_{\text{GS}}=-4.5\text{V}, \text{I}_D=-4.2\text{A}$	-	62	90	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$\text{V}_{\text{DS}}=-15\text{V}, \text{I}_D=-4.5\text{A}$	4	7	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$\text{V}_{\text{DS}}=-15\text{V}, \text{V}_{\text{GS}}=0\text{V}, \text{F}=1.0\text{MHz}$	-	520	-	PF
Output Capacitance	C_{oss}		-	130	-	PF
Reverse Transfer Capacitance	C_{rss}		-	70	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$\text{t}_{\text{d(on)}}$	$\text{V}_{\text{DD}}=-15\text{V}, \text{ID}=-1\text{A}, \text{V}_{\text{GS}}=-10\text{V}, \text{R}_{\text{GEN}}=6\Omega$	-	7	-	nS
Turn-on Rise Time	t_r		-	13	-	nS
Turn-Off Delay Time	$\text{t}_{\text{d(off)}}$		-	14	-	nS
Turn-Off Fall Time	t_f		-	9	-	nS
Total Gate Charge	Q_g		-	11	-	nC
Gate-Source Charge	Q_{gs}	$\text{V}_{\text{DS}}=-15\text{V}, \text{I}_D=-5.1\text{A}, \text{V}_{\text{GS}}=-10\text{V}$	-	2.2	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_s=-5.1\text{A}$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

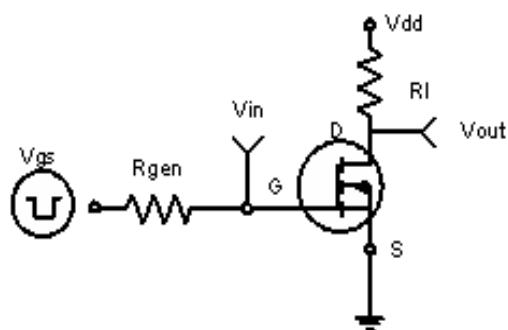


Figure 1:Switching Test Circuit

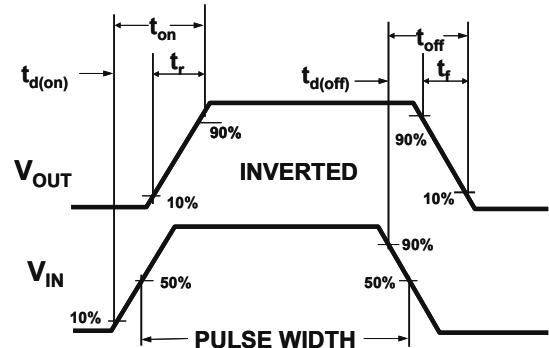
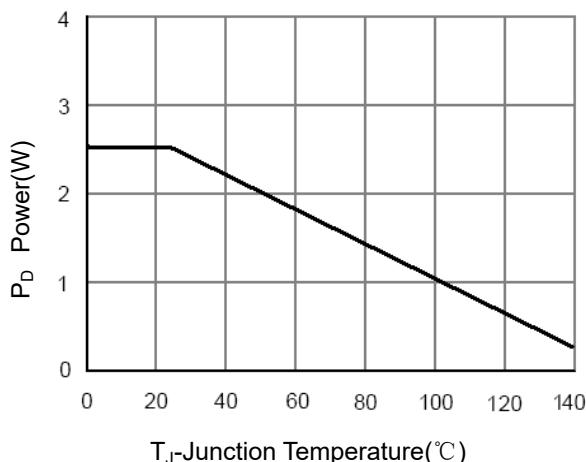
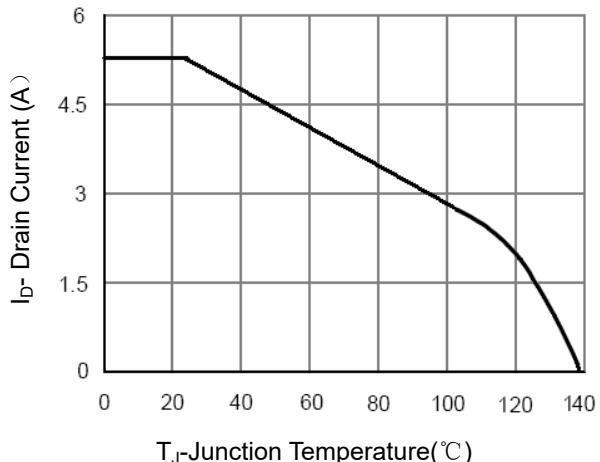


Figure 2:Switching Waveforms



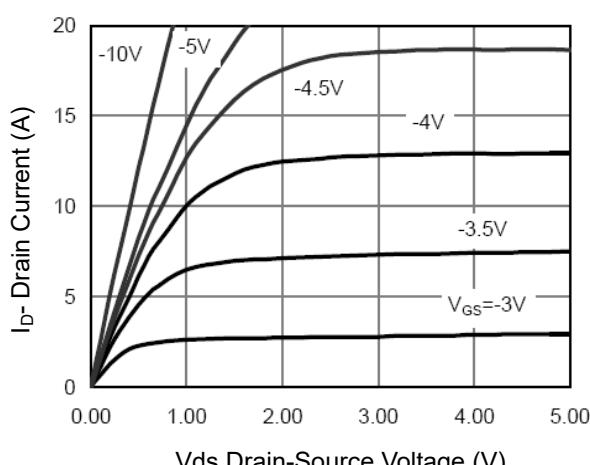
T_j-Junction Temperature(°C)

Figure 3 Power Dissipation



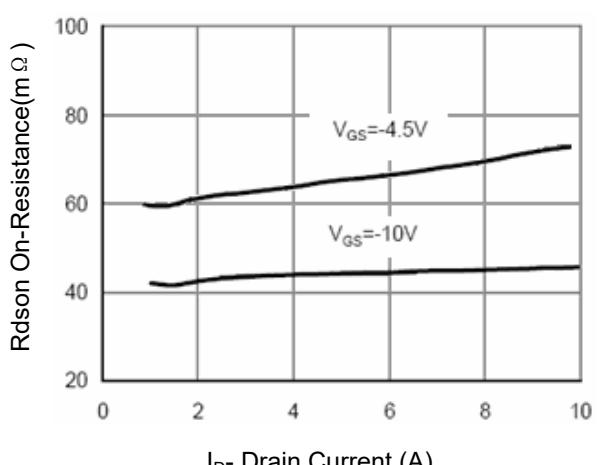
T_j-Junction Temperature(°C)

Figure 4 Drain Current



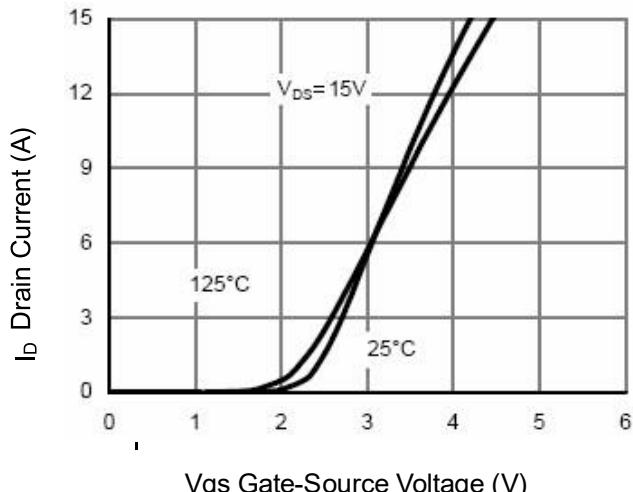
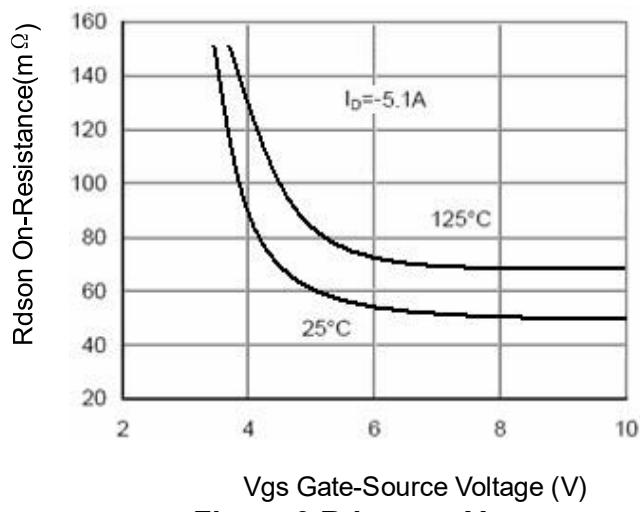
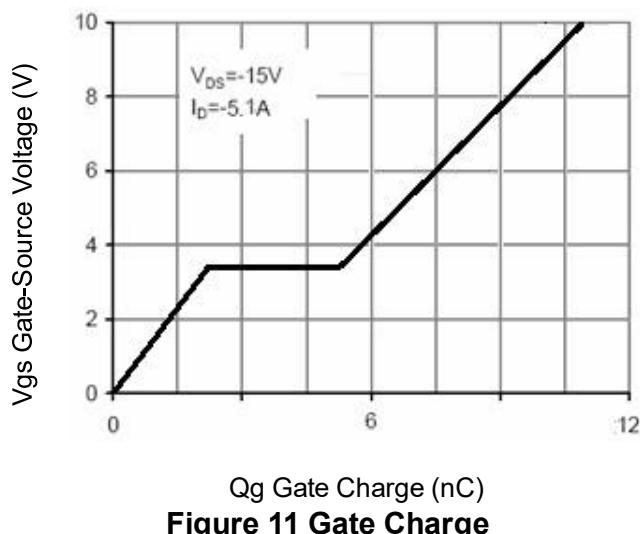
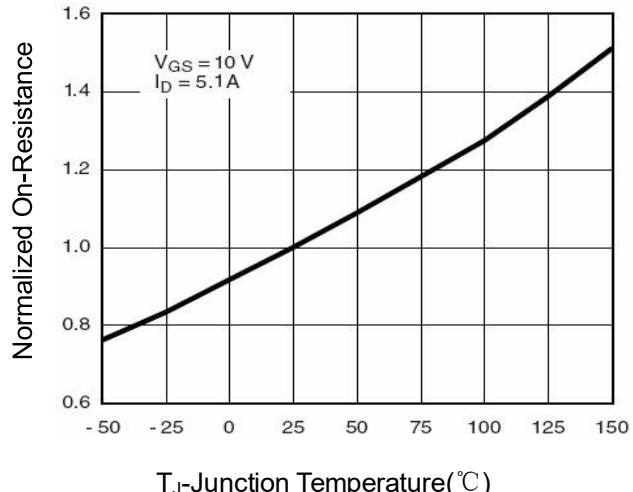
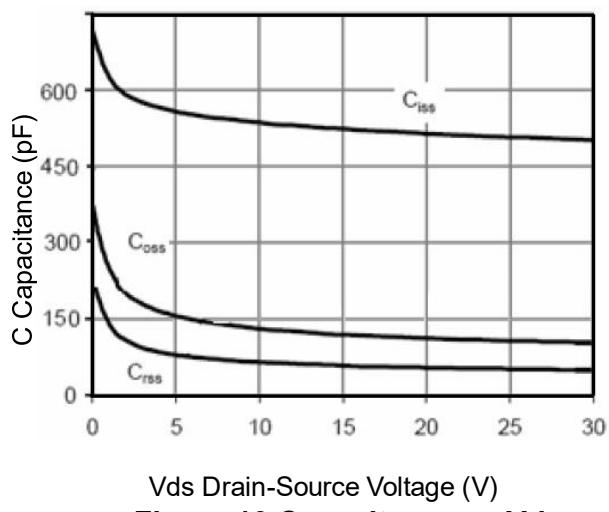
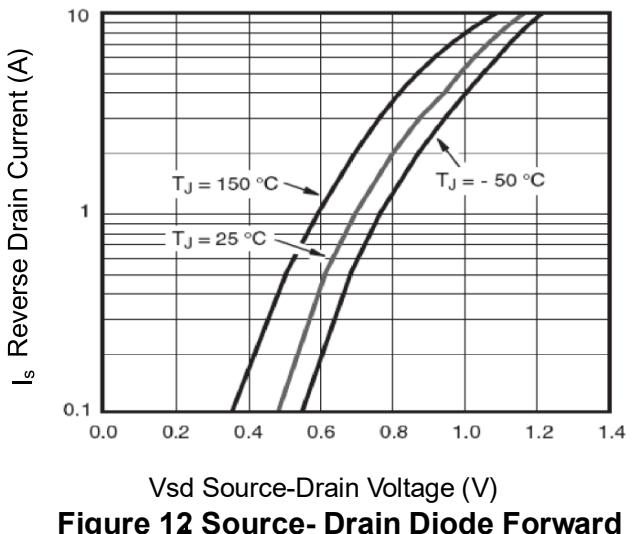
V_{ds} Drain-Source Voltage (V)

Figure 5 Output Characteristics



I_D- Drain Current (A)

Figure 6 Drain-Source On-Resistance

Figure 5 Output Characteristics

Figure 7 Transfer Characteristics

Figure 9 Rdson vs Vgs

Figure 11 Gate Charge

Figure 8 Drain-Source On-Resistance

Figure 10 Capacitance vs Vds

Figure 12 Source-Drain Diode Forward

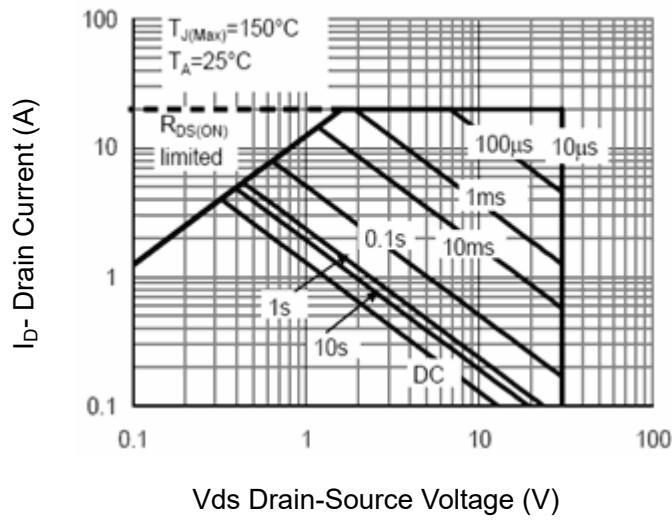


Figure 13 Safe Operation Area

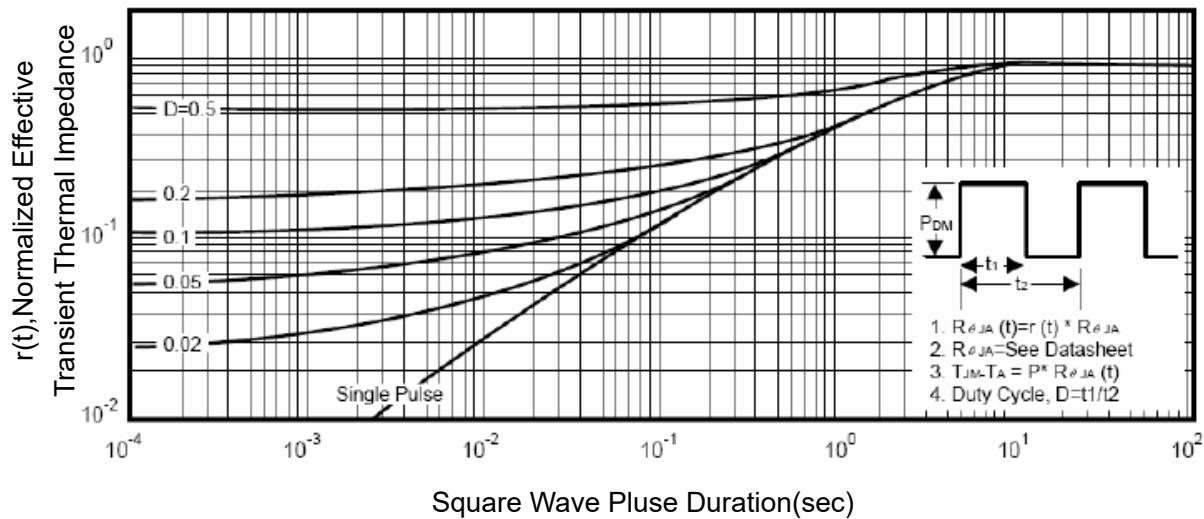
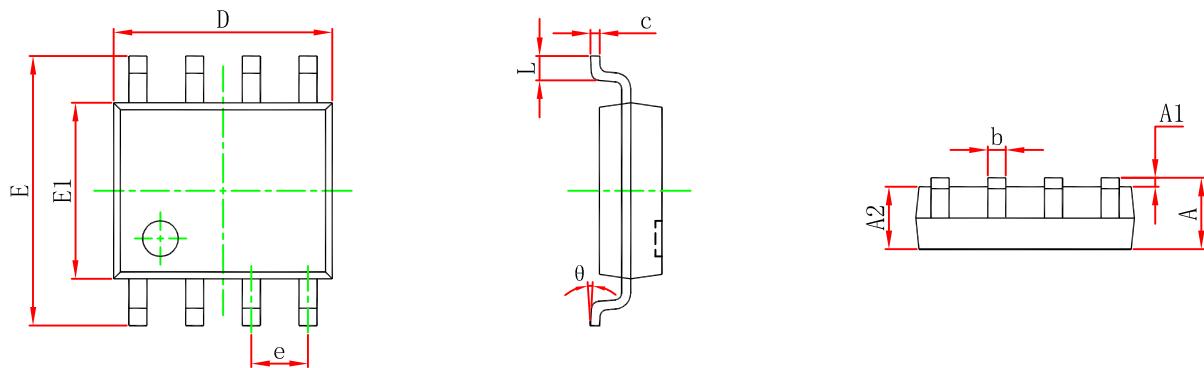
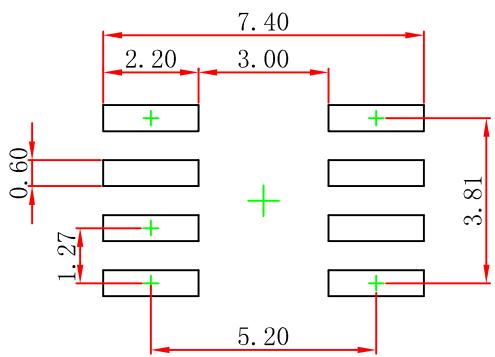


Figure 14 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.